

ABSTRACT

The present invention relates to a method of forming a thin film in a semiconductor device. According to the method, the thin film is formed by
5 alternately repeating an atomic layer deposition (ALD) method and a plasma enhanced atomic layer deposition (PEALD) method and further by adjusting the ratio of repetition times of the methods, so that it is possible to adjust and estimate the growth rate, density, and material properties such as refraction index, dielectric constant, electric resistance, etc.